HOPPLUS, INSTERC, JAPAO, US PATALL)

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L13 ANSWER 1 OF 1 USPATFULL on STN
           The present invention relates to silicon feedstock
           for producing directionally solidified
           silicon ingots, thin sheets and ribbons for
           the production of silicon wafers for PV solar cells where the
           silicon feedstock contains between 0.2 and 10 ppma
          boron and between 0.1 and 10 ppma phosphorus distributed in the material. The invention further relates to directionally solidified silicon ingot or thin silicon sheet or ribbon for making wafers for solar cells containing between 0.2 ppma and 10 ppma boron and between 0.1 ppma and 10 ppma phosphorus distributed in the ingot, said silicon ingot having a type change from p-type to n-type or from n-type to p-type at a position between 40 and 99% of the ingot height or sheet or ribbon thickness and having a resistivity profile described by an exponential curve having a starting value between 0.4 and 10 ohm cm and where the resistivity value increases towards the type change point. Finally the invention relates to a method for producing silicon feedstock for producing directionally solidified silicon ingots thin sheets and ribbons for the production of silicon wafers for PV solar cells.
          boron and between 0.1 and 10 ppma phosphorus distributed in the
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
ΑN
           2007:147006 USPATFULL
           Silicon feedstock for solar cells
TΤ
ΙN
           Enebakk, Erik, Kristiansand, NORWAY
           Friestad, Kenneth, Kristiansand, NORWAY
           Tronstad, Ragnar, Sogne, NORWAY
           Zahedi, Cyrus, Sandvika, NORWAY
           Dethloff, Christian, Oslo, NORWAY
PA
           ELKEM ASA, Oslo, NORWAY, 0377 (non-U.S. corporation)
PΙ
           US 2007128099 ,
                                      A1 20070607
           US 2004-585004
AΙ
                                                20040112 (10)
                                         A1
           WO 2004-NO3
                                                20040112
                                                20060628 PCT 371 date
PRAI
           NO 2003-5830
                                         20031229
           Utility
FS
           APPLICATION
LREP
           LUCAS & MERCANTI, LLP, 475 PARK AVENUE SOUTH, 15TH FLOOR, NEW YORK, NY,
           10016, US
CLMN
           Number of Claims: 9
ECL
           Exemplary Claim: 1
           1 Drawing Page(s)
LN.CNT 297
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
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        (FILE 'HOME' ENTERED AT 16:24:13 ON 07 NOV 2007)
       FILE 'ABI-INFORM, INSPEC, JAPIO, USPATFULL, USPATOLD, USPAT2' ENTERED AT
       16:24:49 ON 07 NOV 2007
L1
                   560 S (SI OR SILICON) (8A) (FEEDSTOCK)
L2
               12708 S (FZ OR FLOAT (2W) ZONE)
L3
                     O S (MULTICRYSTAL? RO POLYCRYSTAL?) (8A) (INGOT# OR BOULE# OR CRYST
L4
               17150 S (SOLIDIF? (10A) DIRECT?)
L5
               38650 S (CZ OR CZOCHRALSKI)
L6
               59572 S (SHEET# AND RIBBON#)
L7
             154055 S (SI OR SILICON) (8A) (WAFER#)
\Gamma8
                   622 S (PV(6A)SOLAR(3W)CELL#)
L9
            5600997 S (B OR BORON)
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L10 L11 L12 L13	3525187 S (P OR PHOSPHORUS) 1 S L1 AND L2 AND L4 AND L5 AND L6 AND L9 AND L10 1 S L1 AND L2 AND L4 AND L5 AND L6 1 S L1 AND L2 AND L4 AND L5 AND L6	

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(FILE 'HOME' ENTERED AT 16:24:13 ON 07 NOV 2007)

FILE 'ABI-INFORM, INSPEC, JAPIO, USPATFULL, USPATOLD, USPAT2' ENTERED AT 16:24:49 ON 07 NOV 2007 L1560 S (SI OR SILICON) (8A) (FEEDSTOCK) 12708 S (FZ OR FLOAT (2W) ZONE) L2 0 S (MULTICRYSTAL? RO POLYCRYSTAL?)(8A)(INGOT# OR BOULE# OR CRYST L3 17150 S (SOLIDIF?(10A)DIRECT?) L438650 S (CZ OR CZOCHRALSKI) L5 L6 59572 S (SHEET# AND RIBBON#) 154055 S (SI OR SILICON) (8A) (WAFER#) L7 L8 622 S (PV(6A)SOLAR(3W)CELL#) L9 5600997 S (B OR BORON) L10 3525187 S (P OR PHOSPHORUS) \Rightarrow s 11 and 12 and 14 and 15 and 16 and 19 and 110 L111 L1 AND L2 AND L4 AND L5 AND L6 AND L9 AND L10 => d l1 abs,bib ANSWER 1 OF 560 ABI/INFORM COPYRIGHT 2007 ProQuest Information and

- L1Learning Company; All Rights Reserved on STN
- The photovoltaic industry has been growing with astonishing rates over the AB past years. The supply of silicon to the wafer-based industry has recently become a problem. This paper presents a thorough analysis of the PV industry and quantifies the silicon shortage. It is expected that this leads to a decrease in production in 2006 rather than the usual increase. Due to a mismatch in expansion plans of silicon feedstock manufacturers and solar cell manufacturers, a large cell overcapacity will persist up to 2010. The thin-film PV market is expected to profit from the silicon shortage problem; its market share may substantially increase to about 25% in 2010. [PUBLICATION ABSTRACT] AN

2007:63604 ABI-INFORM

- DN 1258159731
- ΤI Analysis of the silicon market: Will thin films profit?
- ΑU Brandsen, G W; Fleuster, M; Hekkert, M P
- SO Energy Policy: Publisher: Kidlington, (2007) Vol. 35, No. 6, p. 3121. Journal code: ENP; 17184. AVAILABILITY: NO CODEN: ENPYAC; ISSN: 0301-4215.
- DTJOURNAL
- TC PERIODICAL
- LA English
- ED Entered STN: 1 Jun 2007

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Donald Chucas TEL #(34) 66/-8000 Fey #(313) 661-8002

14/585,004

Examiner's Notes

M 903 (03/08/2007)

X Red US, Pat No. 4, 247, 528 A (Dasay, etal) Clarus 2-689

Helected Product Clairs 1-8 on 10/3/2007,

S(Si or silicon) (10a) (feedstock) S(FZ or float (u) zone)

(S (multicrystal? or polyarysital?) (8a) (ingot # or boule# or crystal#) s(solidif?) [10a) (direction?) or (solidif? (Ba) direct?)

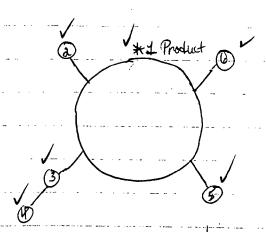
S(CZ or ezochtalki) S(Sheet# and ribbon#)

S (Si or silicen) (80) (water#) S (DV (la) solar (2w) ceil#)

S (B or becon) S (Per phosphorus)

18/149,176

42/92/813



= *7 Product

Clarus 1-4 over US, Pat# 4,247,508A

112Pa Ke .. characterized in that ... "

- Allowable Subi Matter Claims 768

Analysis of the Silicon market: Will thin files profit?

Brandsen, G.W; Flewster, M; HeKKert, MP.

Energy Policy & Publisher: Kid lington, Soozy Vol. 35, No. 6, p. 3121.

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